

N-Channel Enhancement Mode MOSFET

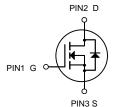
Description

The IRLM0060TRPBF uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

 $V_{DS} = 60V I_{D} = 3A$ $R_{DS(ON)}$ < $89m\Omega$ @ V_{GS} =10V



Application

Battery protection Load switch Uninterruptible power supply

N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRLM0060TRPBF	SOT-23	S10	3000PCS

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	60	V
V _G s	Gate-Source Voltage	±20	V
l _D	Drain Current-Continuous	3	А
Ім	Drain Current-Pulsed (Note 1)	10	А
Po	Maximum Power Dissipation	1.7	W
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C
Rеја	Thermal Resistance,Junction-to-Ambient (Note 2)	73.5	°C /W

N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	_	_	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	8.0	1.3	2.0	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I_D =3A	-	80	89	mΩ	
Drain-Oddrec On-State Resistance		V_{GS} =4.5V, I_{D} =1.5A	-	89	115	mΩ	
Forward Transconductance	g FS	V _{DS} =15V,I _D =2A		3	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	\/ -20\/\/ -0\/	-	510	-	PF	
Output Capacitance	Coss	V_{DS} =30V, V_{GS} =0V, F=1.0MHz	-	34	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.0WHZ	-	26	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	6	-	nS	
Turn-on Rise Time	t _r	V _{DD} =30V,I _D =1.5A	-	15	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =1 Ω	_	15	-	nS	
Turn-Off Fall Time	t _f		-	10	-	nS	
Total Gate Charge	Qg	\/ -20\/ L -2A	-	7.5	-	nC	
Gate-Source Charge	Q_{gs}		-	1.4	-	nC	
Gate-Drain Charge	Q_{gd}	V _{GS} -4.5V	-	3	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =3A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	3	Α	
Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Drain-Source Diode Characteristics Diode Forward Voltage (Note 3)	$\begin{array}{c} t_f \\ Q_g \\ Q_{gs} \\ Q_{gd} \\ \end{array}$	V _{DS} =30V,I _D =3A, V _{GS} =4.5V		10 7.5 1.4	1.2	nS nC nC	

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

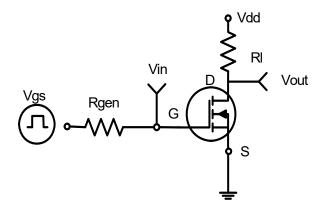


Figure 1:Switching Test Circuit

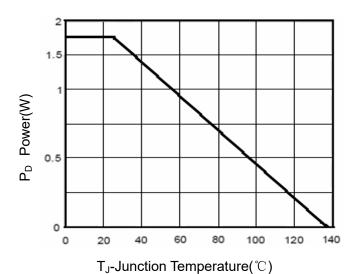


Figure 3 Power Dissipation

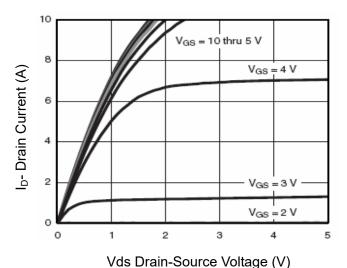


Figure 5 Output Characteristics

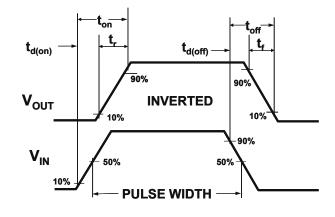


Figure 2:Switching Waveforms

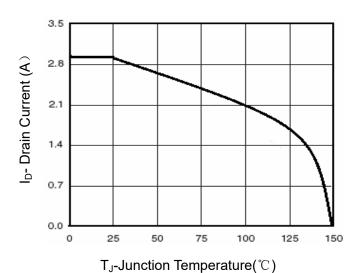


Figure 4 Drain Current

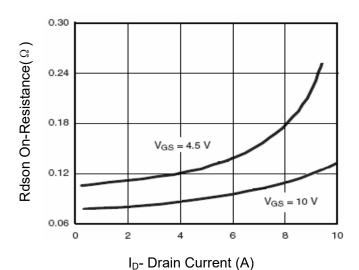


Figure 6 Drain-Source On-Resistance

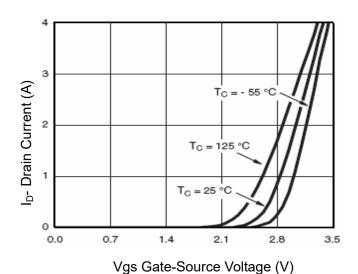
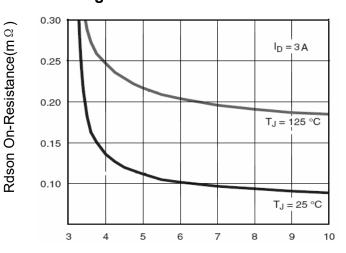
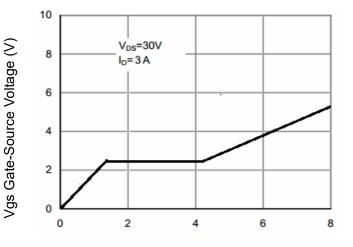


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs



Qg Gate Charge (nC) Figure 11 Gate Charge

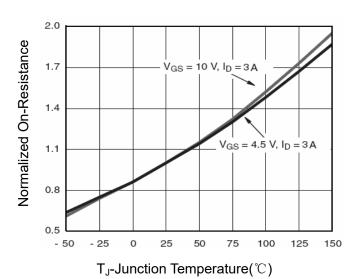


Figure 8 Drain-Source On-Resistance

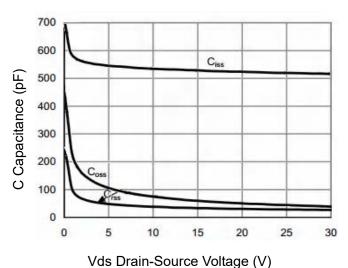


Figure 10 Capacitance vs Vds

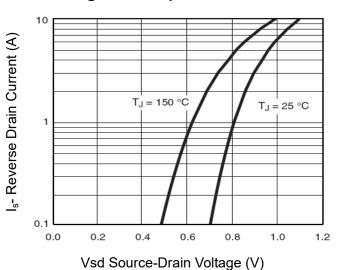


Figure 12 Source- Drain Diode Forward

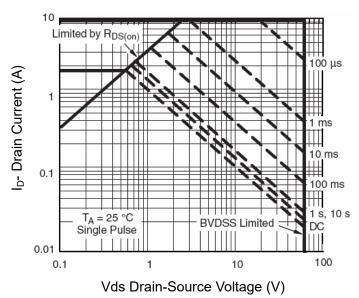


Figure 13 Safe Operation Area

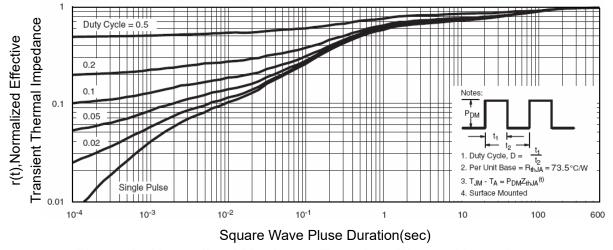
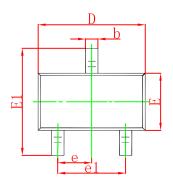
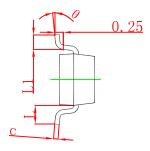


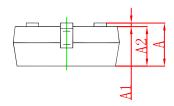
Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Outline Dimensions

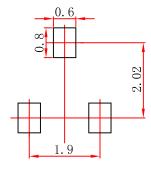






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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